1A1 THRU 1A7

GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts   Forward Current - 1.0 Ampere

R-1

1.0 (25.4) MIN.

0.102 (2.6) / 0.091 (2.3) DIA.

0.140(3.50) / 0.114(2.90)

1.0 (25.4) MIN.

0.025 (0.65) / 0.021 (0.55) DIA.

Dimensions in inches and (millimeters)

FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed: 250℃/10 seconds,0.375"(9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: R-1 molded plastic body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight:0.007 ounce, 0.20 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
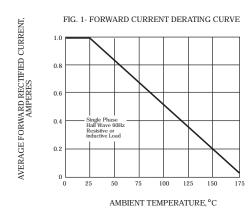Single phase half-wave 60Hz,resistive or inductive load,for capacitive load current derate by 20%.

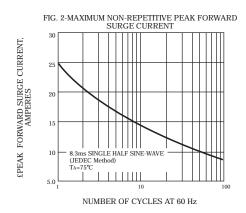|	SYMBOLS	1A1	1A2	1A3	1A4	1A5	1A6	1A7	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current 0.375"(9.5mm) lead length at T_A=25℃	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	25.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							Volts
Maximum DC reverse current T_A=25℃ at rated DC blocking voltage T_A=100℃	I_R	5.0 50.0							mA
Typical junction capacitance (NOTE 1)	C_J	15.0							pF
Typical thermal resistance (NOTE 2)	R_{qJA}	50.0							℃/W
Operating junction and storage temperature range	T_J, T_{STG}	-50 to +150							℃

Note:1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.
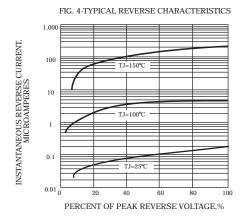2.Thermal resistance from junction to ambient at 0.375"(9.5mm)lead length,P.C.B. mounted

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Runji Semi-Conductor Ltd

RATINGS AND CHARACTERISTIC CURVES 1A1 THRU 1A7

FIG. 1- FORWARD CURRENT DERATING CURVE

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

FIG. 4-TYPICAL REVERSE CHARACTERISTICS

FIG. 5-TYPICAL JUNCTION CAPACITANCE

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE

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